HITANO ENTERPRISE CORP.

1N914 THRU 1N4148~1N4454

TECHNICAL SPECIFICATIONS OF HIGH SPEED SWITCHING DIODES

VOLTAGE RANGE -50 to 100 Volts CURRENT - 0.075 to 0.2 Ampere

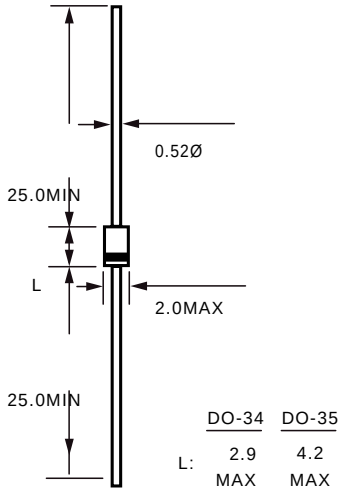
FEATURES

* Silicon epitaxial planar diodes
* Low power loss, high efficiency
* Low leakage
* Low forward voltage
* High speed switching
* High current capability
* High reliability

MECHANICAL DATA

* Case: Glass sealed case
* Lead: MIL-STD-202E, Method 208 guaranteed
* Polarity: Color band denotes cathode end
* Mounting position: Any
* Weight: 0.13 gram

DO-34 / DO-35



L:	DO-34	DO-35
	2.9 MAX	4.2 MAX

Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

	SYMBOL	1N914	1N4148	1N4150	1N4151	1N4154	1N4448	1N4454	UNITS
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	100	100	50	75	35	100	75	V
Maximum Average Rectified Current	Io	75	150	200	150	150	150	150	mA
Maximum Power Dissipation Tamb=25°C	Ptot	250	500	500	500	500	500	500	mW
Maximum Forward Voltage	V_F	1.0/10	1.0/10	1.0/200	1.0/50	1.0/30	1.0/100	1.0/10	V/mA
Maximum Reverse Current	I_R	5000/75	5000/75	100/50	50/50	100/25	5000/75	100/10	nA/V
Maximum Reverse Recovery Time	trr	4.0	4.0	4.0	2.0	2.0	4.0	4.0	nS
Typical Junction Capacitance	C_J	4.0							pF
Operating and Storage Temperature Range	T_J,T_{STG}	-65 to + 200							°C

NOTE: 1-1N914A, 1N914B IS SAME AS 1N914, EXCEPT DIFFERENT IN FORWARD VOLTAGE:
1N914A-1.0/20 V/mA
1N914B-1.0/100 V/mA
2.Suffix "M" stands for "DO-34" package.(e.g.:1N4148M)

RATING AND CHARACTERISTIC CURVES

(1N914 THRU 1N4148 1N4454)

REF: 1N4148